



# MXDLN02C

## FM Low Noise Amplifier



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### General Description

MXDLN02C low current, high gain, low noise amplifier (LNA) is dedicated to FM receive. This product achieved excellent noise figure of 1.3dB and 23dB gain.

MXDLN02C works under a 2.5V to 3.3V single power supply while consumes 10 mA current, in power down (PD) mode, the power consumption will be reduced to less than 0.1uA.

MXDLN02C uses a small 2.1mmx2.3mmx0.95mm SOT363 6-pin package.

### Applications

Cell Phone with FM  
Portable audio device

### Features

- Low noise figure: 1.3 dB
- High gain: 23dB
- PD current less than 0.1uA
- Single supply voltage range 2.5V to 3.3V
- Small package 2.1mmx2.3mmx0.95mm
- Low cost BOM
- Lead-Free and RoHS-Compliant

### Pin Configuration and function block diagram (Top view)

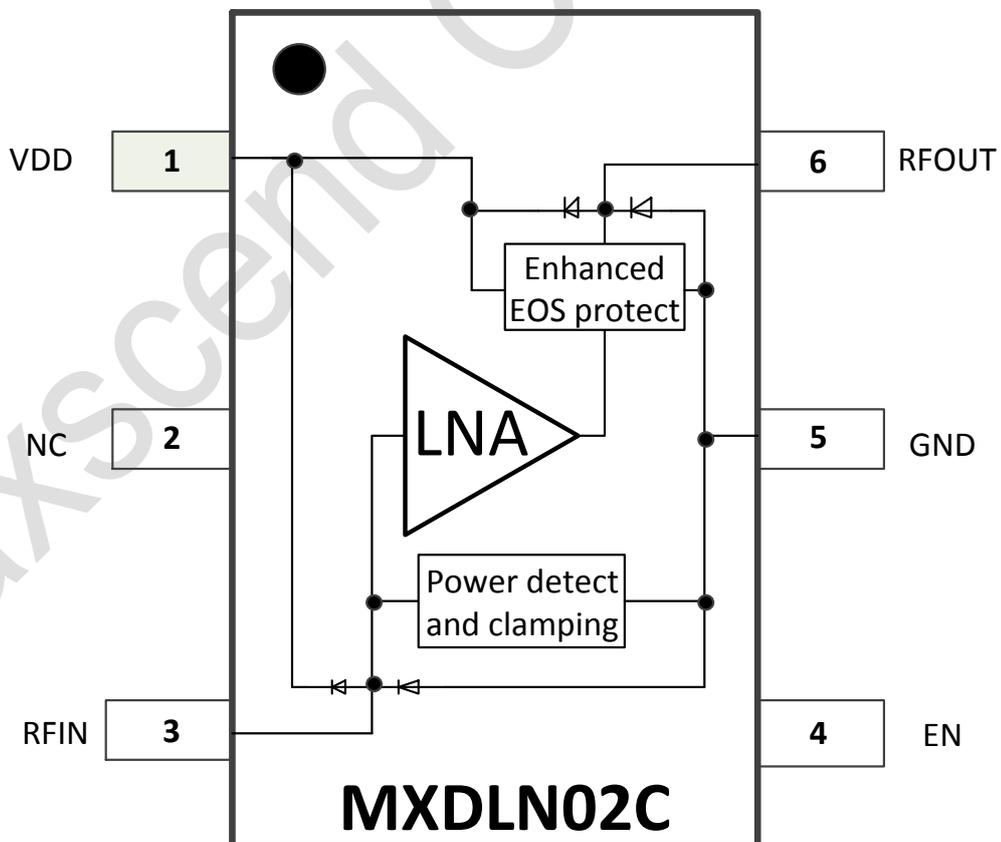


Figure 1 MXDLN02C pin configuration and function block diagram

## Application circuit

Application A: Internal antenna;

Application B: Separated antenna, matching to 50 Ohm.

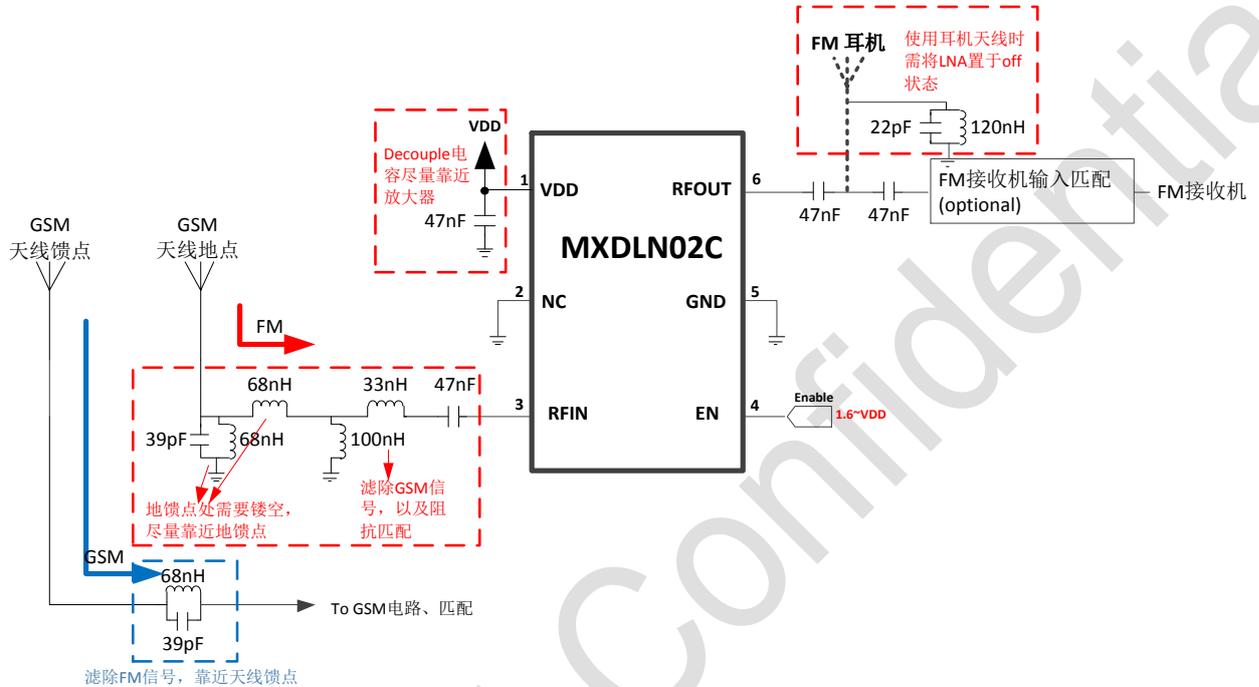


Figure 2 Application A: Internal antenna sharing with GSM

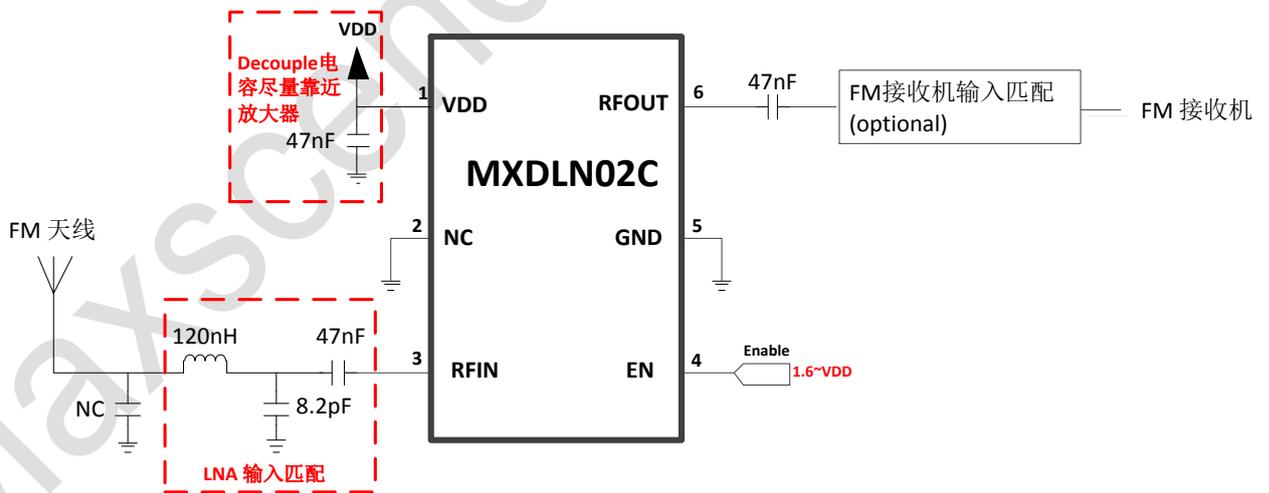


Figure 3 Application B: Separated antenna

## Pin Descriptions

**Table 1. Pin Descriptions**

Pin	Pin Name	I/O	Pin Description
1	VDD	AP	Power supply
2	NC	-	-
3	RFIN	AI	LNA input from antenna
4	EN	DI	Pull high enable, pull low into power down mode
5	GND	AG	Analog VSS
6	RFOUT	AO	LNA output

**Note:** *DI* (digital input), *DO* (digital output), *DIO* (digital bidirectional), *AI* (analog input), *AO* (analog output), *AIO* (analog bidirectional), *AP* (analog power), *AG* (analog ground)

## Absolute Maximum Ratings

**Table 2.**

Parameters	Range	Units
Power supply	-0.3 ~ 3.8	V
Other Pin to GND	-0.3~VDD+0.3	V
Maximum RF Input Power	25	dBm
Operation Temperature Range	-40~85	°C
Junction Temperature	150	°C
Storage temperature Range	-65~160	°C
Lead Temperature (soldering)	260	°C
Soldering Temperature (reflow)	260	°C
Human Body Mode ESD	-2000~+2000	V
Charge Device Mode ESD	-500~+500	V

## Specifications

### DC Characteristics

Typically  $T_A=25^{\circ}\text{C}$  VDD=2.8V, VEN=1.8V, unless otherwise noted

**Table 3.**

Parameters	Condition	Min	Typ	Max	Units
Supply Voltage		2.5	2.8	3.3	V
Supply Current	EN=High		10		mA
EN Input High		1.6	1.8	VDD	V
EN Input Low		0	0	0.3	V

**AC Characteristics**

 Typically  $T_A=25^{\circ}\text{C}$   $V_{DD}=2.8\text{V}$ ,  $V_{EN}=1.8\text{V}$ , all data measured on Maxscend's EVB, unless otherwise noted

**Table 4. AC Specifications, no any matching network, 50 Ohm port**

Parameters	Conditions	Min	Typ	Max	Units
RF Frequency Range		50		150	MHz
Operation Current			10		mA
Power Down Current				0.1	$\mu\text{A}$
Power Gain	Note1		23		dB
Input Power 1-dB Compression Point			-20		dBm
Noise Figure	Note1		1.3		dB
Input Return Loss	Note1		-3.2		dB
Output Return Loss	Note1		-4.5		dB
Reverse Isolation	Note1		-50		dB
Stability	Note1	2			N/A

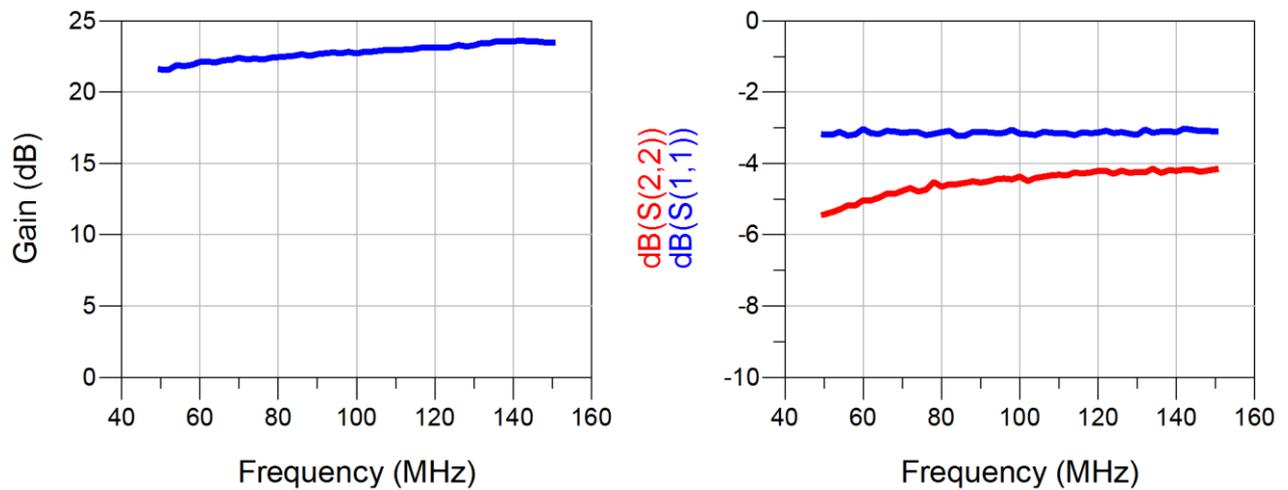
**Note1: measuring at 50 Ohm load**


Figure 4 Power Gain &amp; Input/output return loss

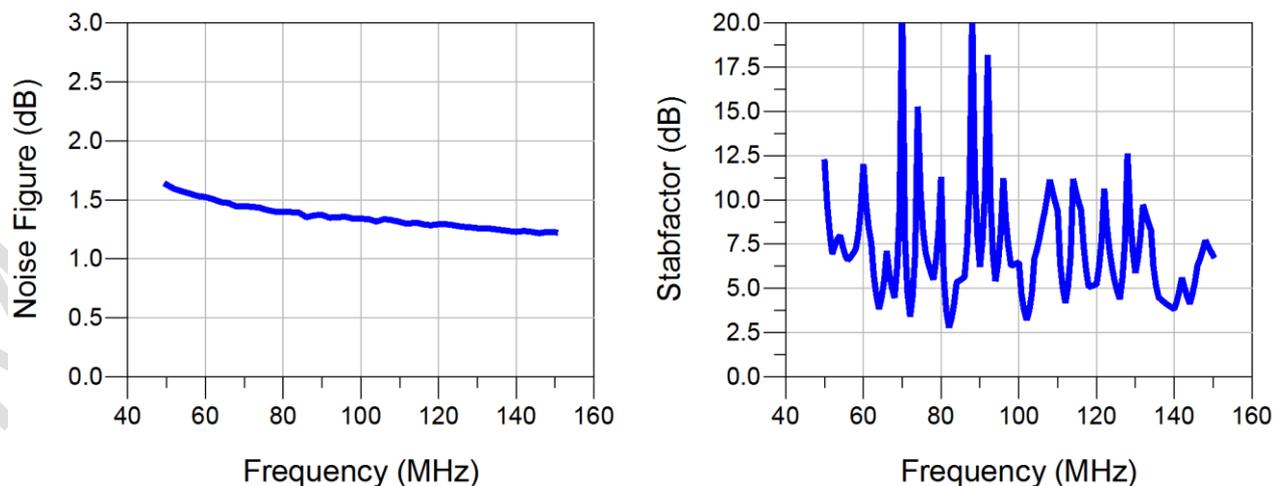


Figure 5 Noise Figure &amp; Stability factor

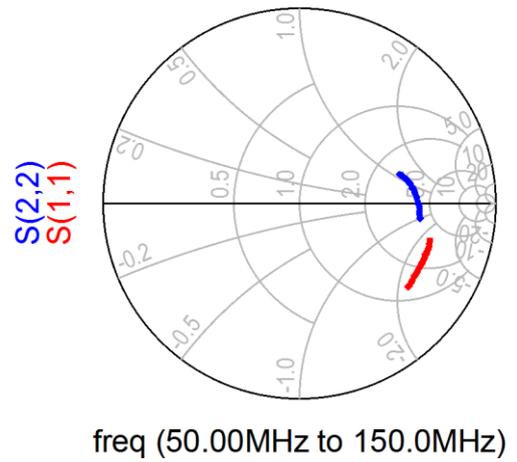
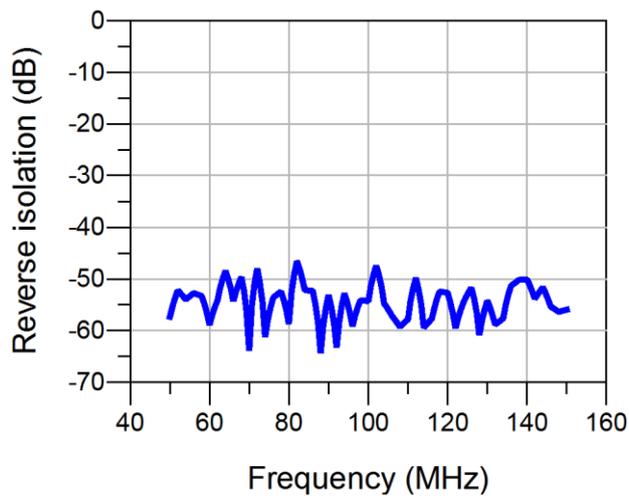


Figure 6 Reverse isolation & Smith chart

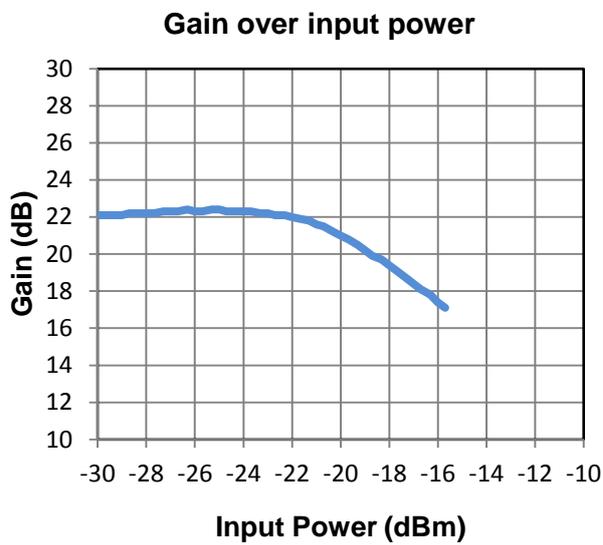
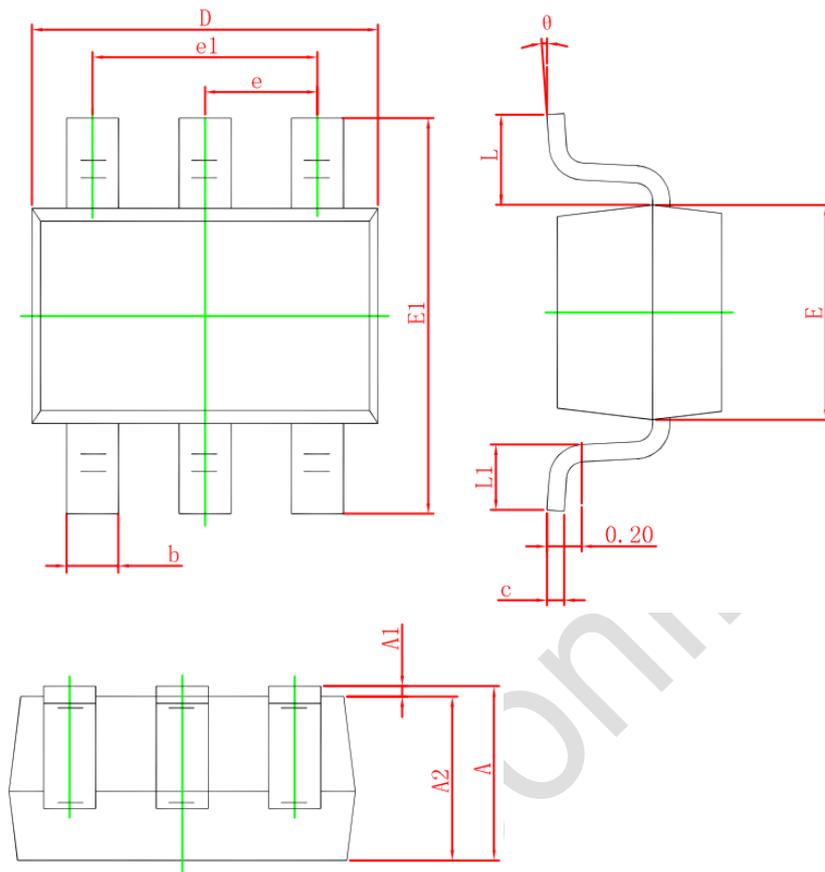


Figure 7 Gain curve over input power

**Package Outline Dimensions**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Figure 8 MXDLN02C outline dimension

## Reflow Chart

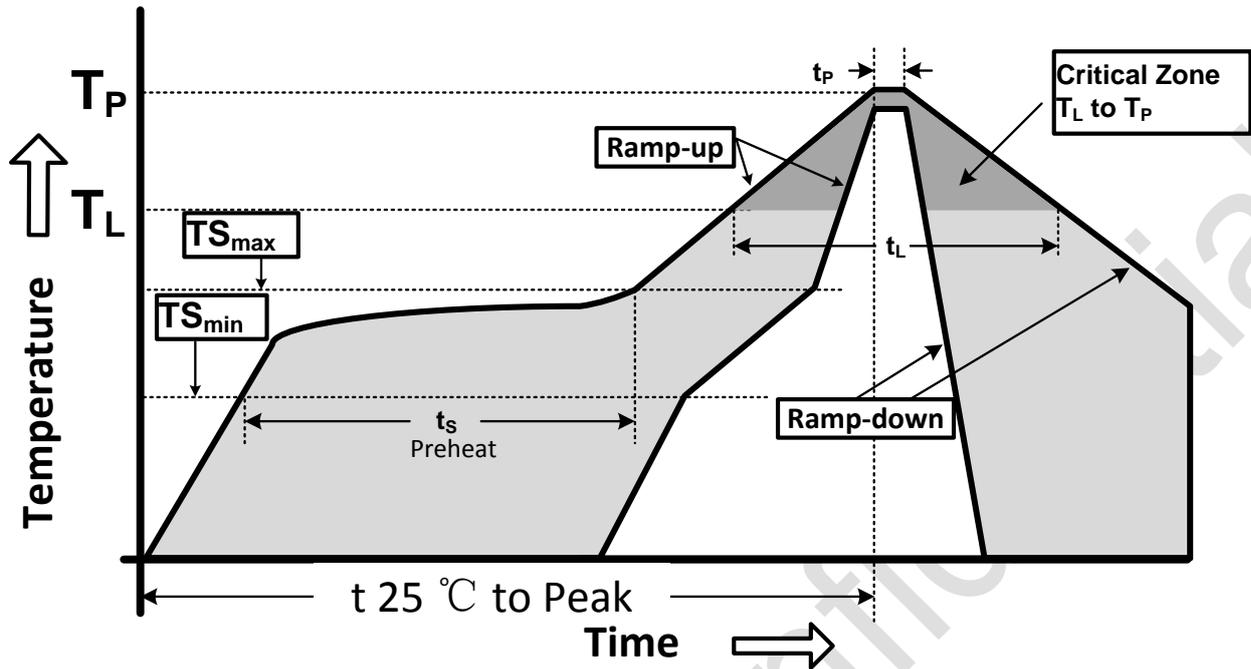


Figure 9 Recommended Lead-Free Reflow Profile

Table 5. Reflow condition

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection
Ramp-up rate ( $TS_{max}$ to $T_p$ )	3°C/second max.
Preheat temperature ( $TS_{min}$ to $TS_{max}$ )	150°C to 200°C
Preheat time ( $t_s$ )	60 - 180 seconds
Time above $T_L$ , 217°C ( $t_L$ )	60 - 150 seconds
Peak temperature ( $T_p$ )	260°C
Time within 5°C of peak temperature( $t_p$ )	20 - 40 seconds
Ramp-down rate	6°C/second max.
Time 25°C to peak temperature	8 minutes max.

**ESD Sensitivity**

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

**RoHS Compliant**

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.

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